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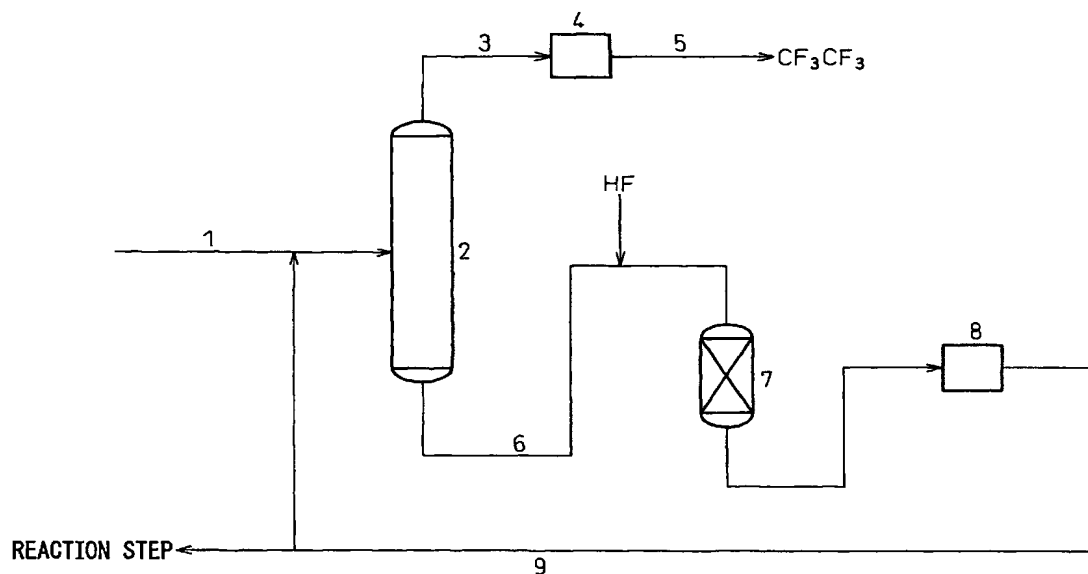
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(54) Title: PROCESS FOR PRODUCING HEXAFLUOROETHANE AND USE THEREOF



(57) Abstract: A process for producing hexafluoroethane, comprising a step of distilling a crude hexafluoroethane containing chlorine compounds each having two carbon atoms to distill out hexafluoroethane as a top flow from the top of a distillation column and separate a hexafluoroethane mixture containing the chlorine compounds as a bottom flow from the bottom, and a step of contacting the bottom flow with hydrogen fluoride in the gas phase at a temperature of 300 to 500 °C in the presence of a fluorination catalyst to fluorinate the chlorine compounds. This process provides hexafluoroethane which can be used mainly as a cleaning gas in the production process of a semiconductor device.



SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

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